

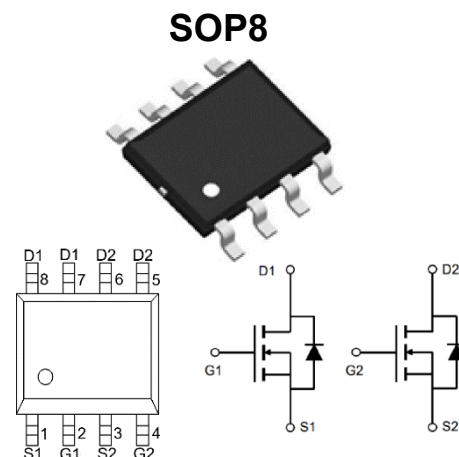
60V_{DS}/±20V_{GS} N-Channel Enhancement Mode MOSFET

Features

- V_{DS}=60V, I_D=7A
- R_{DS(ON)}=35mΩ (TYP.) V_{GS}=10V
- R_{DS(ON)}=50mΩ (TYP.) V_{GS}=4.5V
- Reliable and Rugged
- Avalanche Rated
- Low On-Resistance

Applications

- Load Switch
- Power management in portable/desktop PCs
- DC/DC conversion



Ordering Information

Device	package	Device Marking	Package Qty.
HMN4826AS	SOP-8	N4826AS	3000/PCS

Absolute Maximum Ratings (T_C=25°C, unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage (V _{GS} =0V)	V _{DS}	60	V
Gate-Source Voltage (V _{GS} =0V, static)	V _{GS}	±20	V
Continuous Drain Current (T _C =25°C)	I _D	7	A
Continuous Drain Current (T _C =100°C)		4.5	A
Pulsed Drain Current	I _{DM}	30	A
Single Pulsed Avalanche Energy	E _{AS}	66	mJ
Maximum Power Dissipation (T _C =25°C)	P _D	12	W
Maximum Power Dissipation (T _C =100°C)		5	W
Operating, Storage Temperature Range	T _J , T _{STG}	-55~150	°C

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Case	R _{θJC}	-	6.8	-	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	-	78	-	°C/W

Electrical Characteristics

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$	-	-	1	μA
Gate -Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	1.5	2	V
Drain-Source On-stage Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=1A$	-	28	35	m Ω
		$V_{GS}=4.5V, I_D=1A$	-	30	50	

Dynamic Characteristics

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$V_{DS}=15V$ $V_{GS}=0V$ $f=1MHz$	-	1020	-	pF
Output capacitance	C_{oss}		-	60	-	
Reverse transfer capacitance	C_{rss}		-	45	-	
Gate Resistance	R_g	$f=1MHz$	-	1.9	-	Ω
Total Gate Charge	Q_g	$V_{DS}=15V$ $V_{GS}=10V$ $I_D=20A$	-	23	-	nC
Gate Source Charge	Q_{gs}		-	6.2	-	
Gate Drain Charge	Q_{gd}		-	8.9	-	
Turn-on delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=15V$ $R_L=3.5\Omega$ $R_G=6.8\Omega$	-	15	-	ns
Rise time	t_r		-	28	-	
Turn-off delay Time	$t_{d(off)}$		-	68	-	
Fall time	t_f		-	22	-	

Reverse Diode Characteristics

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Body Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_{SD}=1A$	-	0.7	1	V
Reverse Recovery Time	t_{rr}	$V_{GS}=0V, I_{SD}=20A$ $d_i/d_t=100A/\mu s$	-	17	-	ns
Reverse Recovery Charge	Q_{rr}		-	25	-	nC

Electrical Characteristics Diagrames

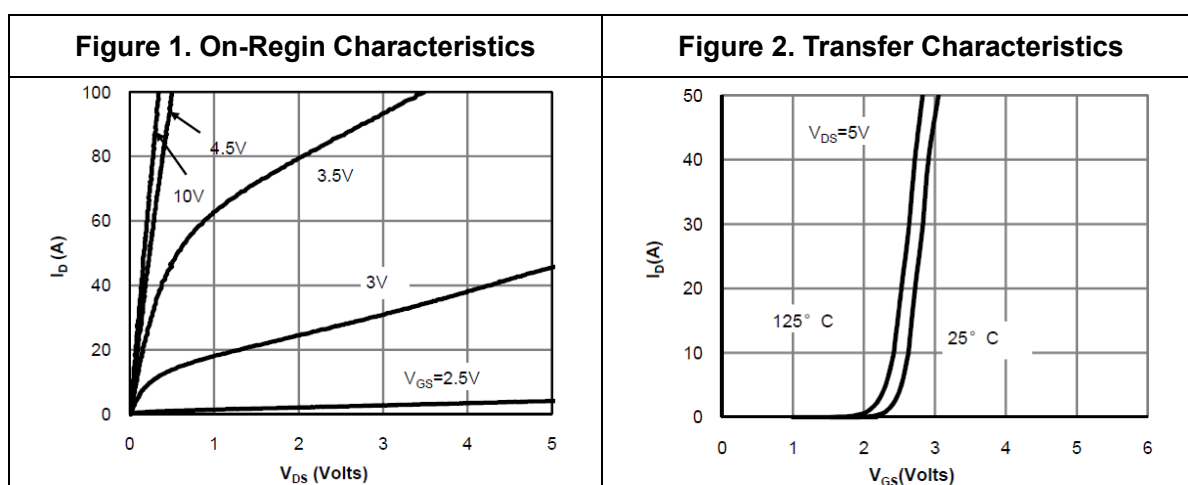


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

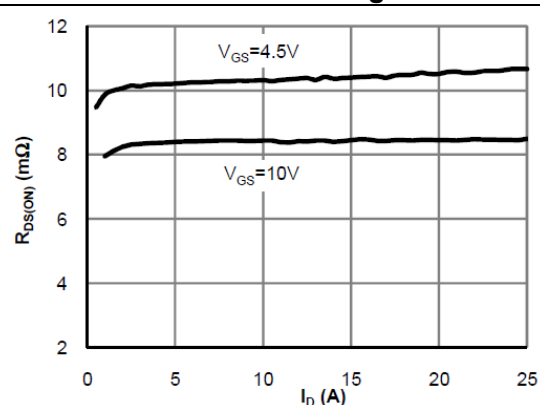


Figure 4. On-Resistance vs. Junction Temperature

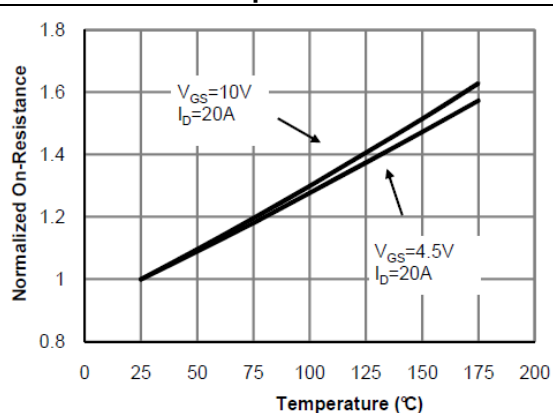


Figure 5. On-Resistance vs. Gate-Source Voltage

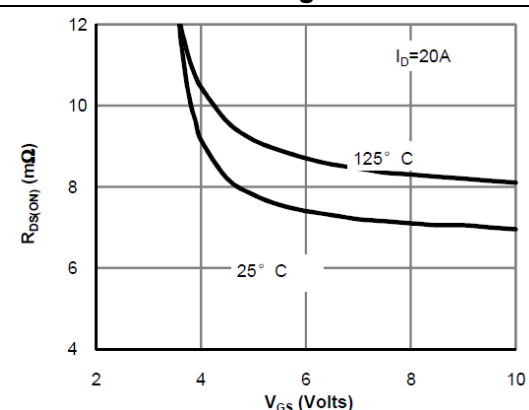


Figure 6. Body-Diode Characteristics

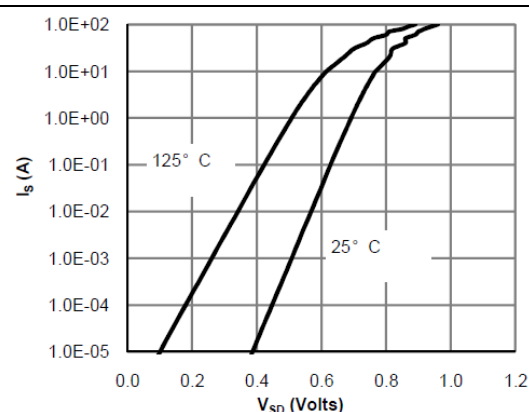


Figure 7. Gate-Charge Characteristics

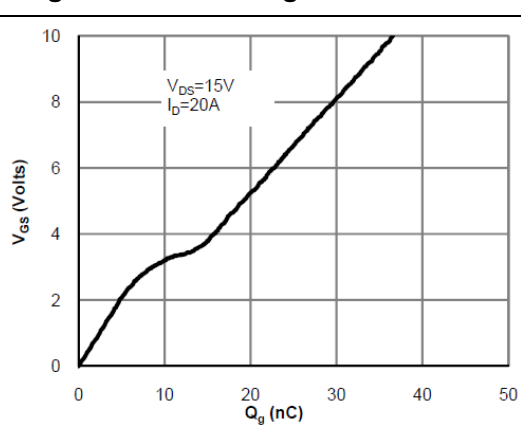


Figure 8. Capacitance Characteristics

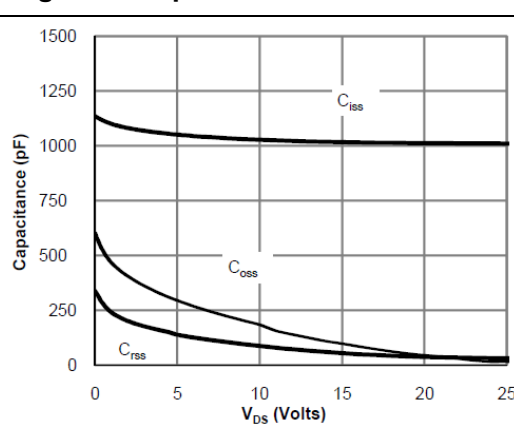


Figure 9. Maximum Forward Biased Safe Operating Area

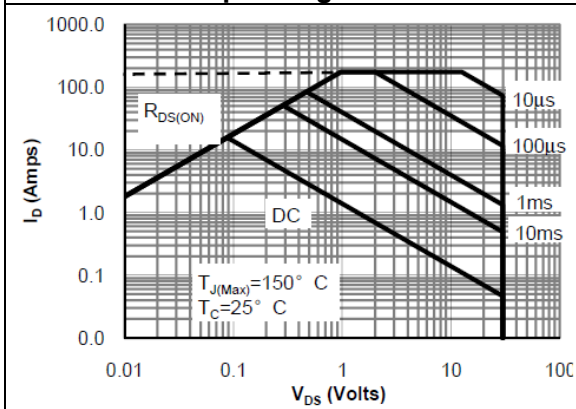


Figure 10. Single Pulse Power Rating Junction-to-Ambient

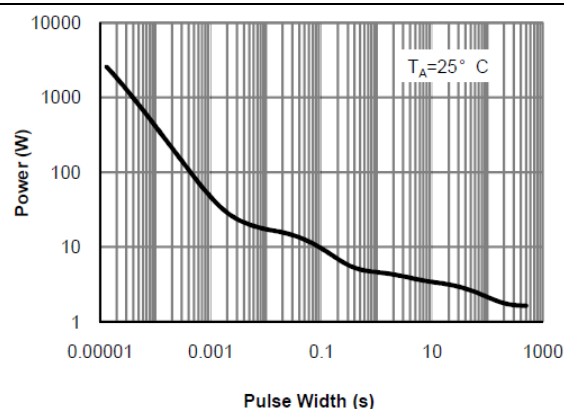
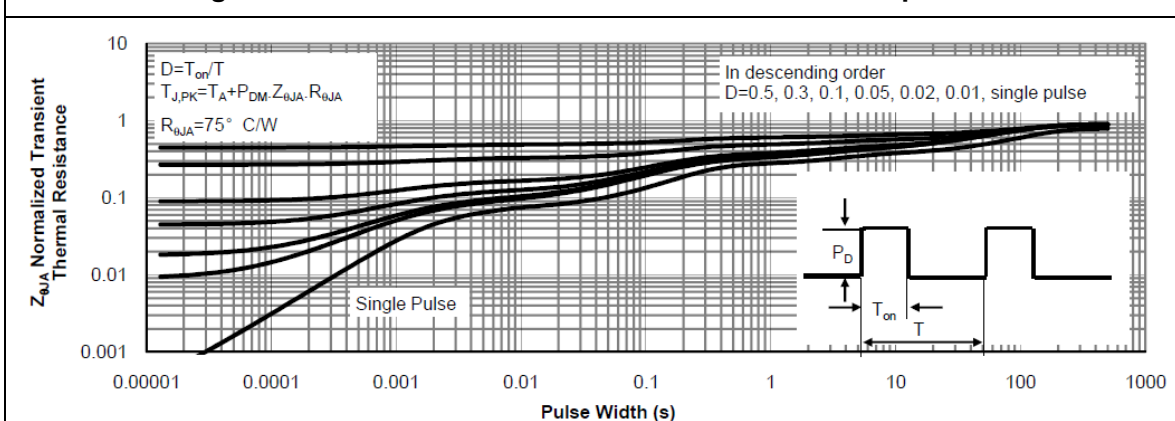
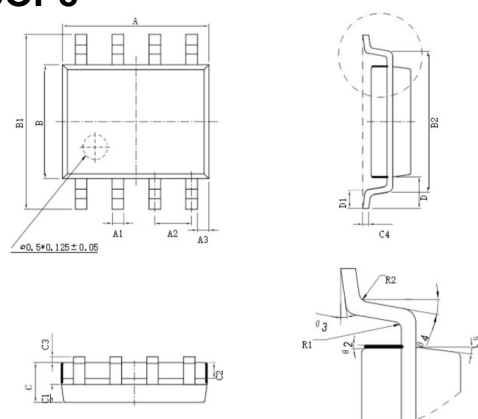


Figure 11. Normalized Maximum Transient Thermal Impedance



Physical Dimensions

SOP8



符号	尺寸 (mm)		符号	尺寸 (mm)	
	最小值	最大值		最小值	最大值
A	4.80	5.00	C3	0.05	0.20
A1	0.356	0.456	C4	0.203	0.233
A2	1.27 TYP		D	1.05 TYP	
A3	0.345 TYP		D1	0.40	0.80
B	3.80	4.00	R1	0.20 TYP	
B1	5.80	6.20	R2	0.20 TYP	
B2	5.00 TYP		θ1	17° TYP4	
C	1.30	1.60	θ2	13° TYP4	
C1	0.55	0.65	θ3	0° ~ 8°	
C2	0.55	0.65	θ4	4° ~ 12°	

< Copyright >

All the Patent, Copyright and IP contained in this document belong to HAMOS, shall not be reproduced, copied, or used in other ways without permission.